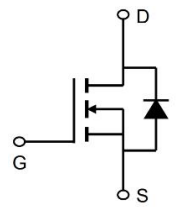
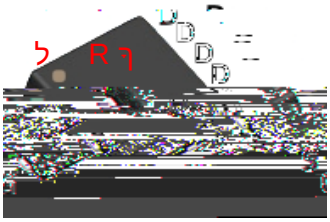
100V N-Channel Enhancement Mode MOSFET

MAIN CHARACTERISTICS

I_D	20A
V_{DSS}	100V
R_{DSON}-typ(@V_{GS}=10V)	<40mΩ**(Typ:33mΩ)**
R_{DSON}-typ(@V_{GS}=4.5V)	<45mΩ**(Typ:35mΩ)**





PDFN3*3-8L

The YFW20N10DF usu s gpcin e RW R 8 E c 4g 4 o R o c

Applications

- Automative lighting
- Load switch
- Uninterruptible power supply

Typical Characteristics

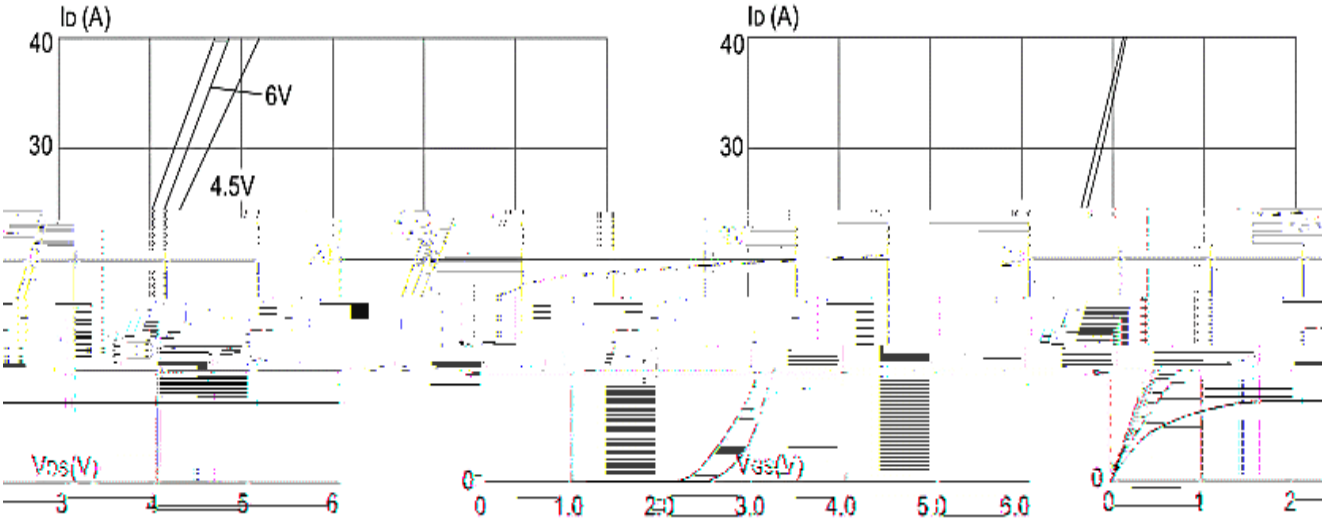


Figure1: Output Characteristics

Figure 2: Typical Transfer Characteristics

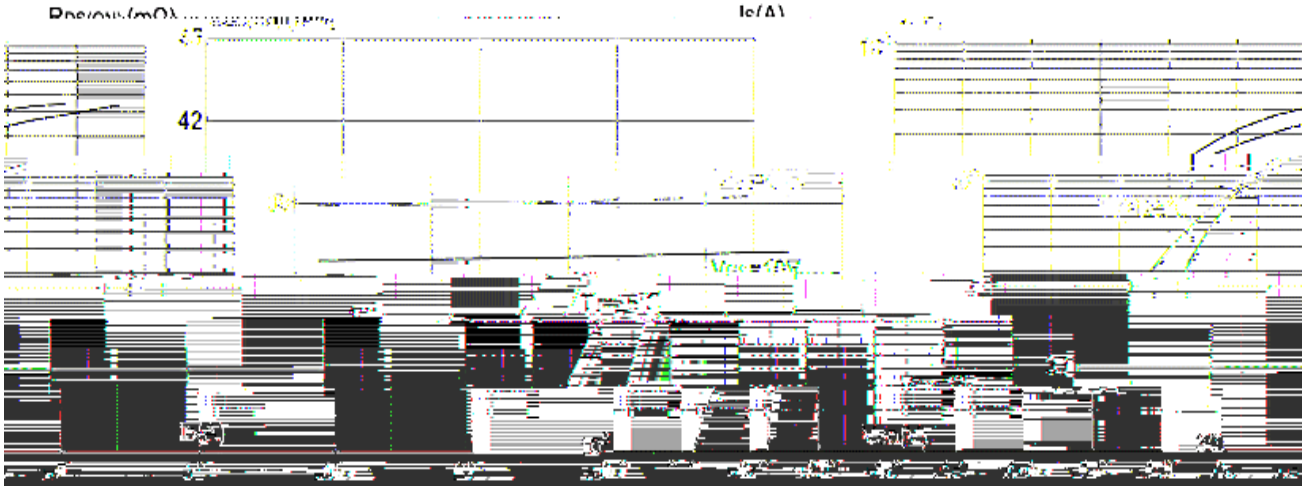


Figure 3:On-resistance vs. Drain Current

Figure 4: Body Diode Characteristics

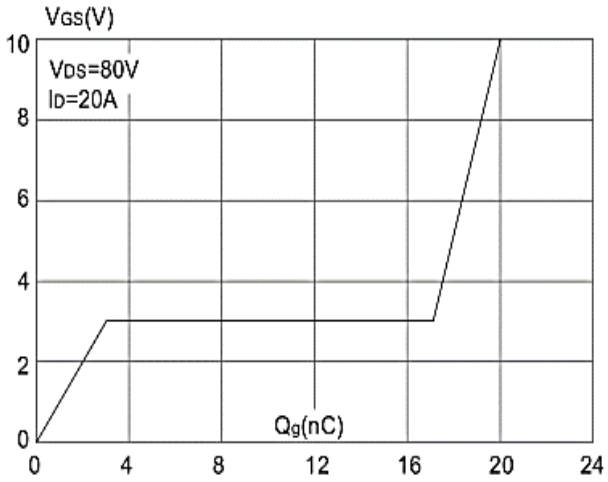


Figure 5: Gate Charge Characteristics

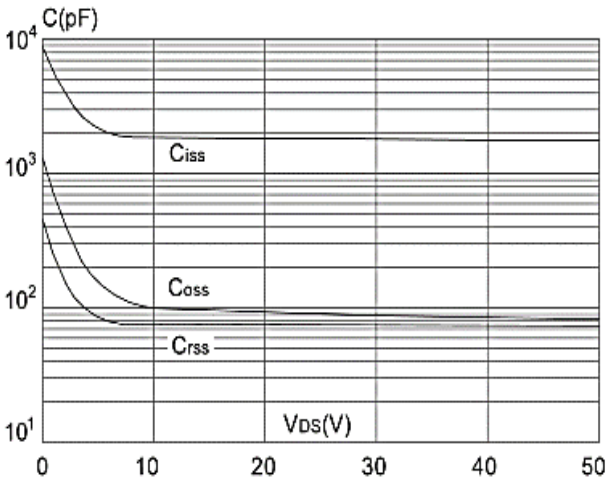


Figure 6: Capacitance Characteristics

Typical Characteristics



Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

Figure 8: Normalized on Resistance vs Junction Temperature

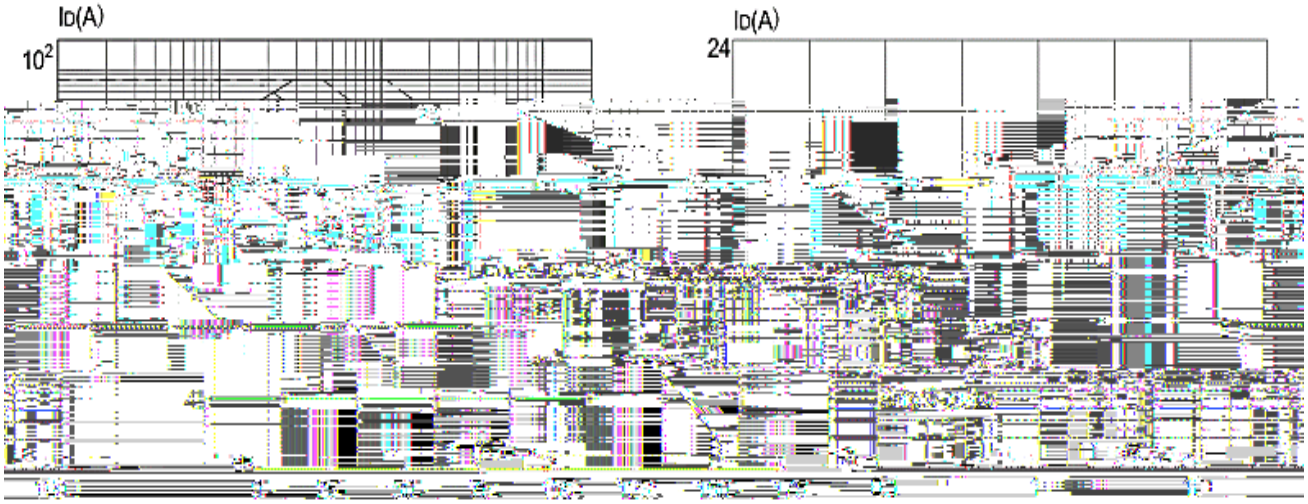


Figure 9: Maximum Safe Operating Area vs. Case Temperature

Figure 10: Maximum Continuous Drain Current

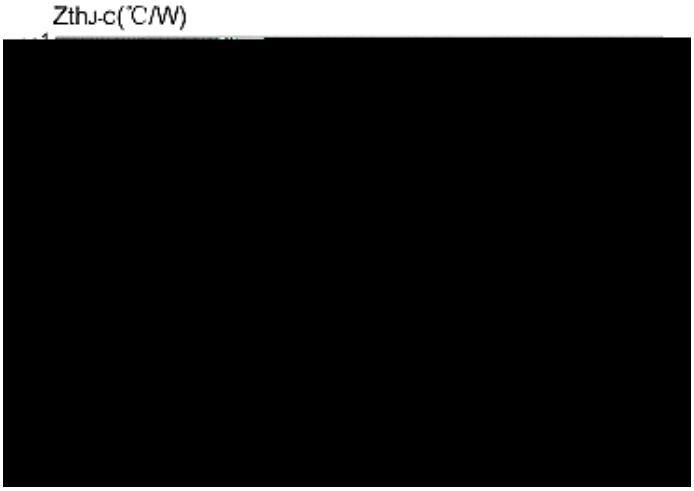


Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Case

Marking Diagram

Ordering information

Model name	Package	Unit Weight	Base Quantity	Packing Quantity
YFW20N10DF				

Package Dimensions

PDFN3*3-8L

Dim	Millimeter		mil	
	Min.	Max.	Min.	Max.

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